

# SEMICONDUCTOR

## TECHNICAL DATA

# MPS8550

## EPITAXIAL PLANAR PNP TRANSISTOR

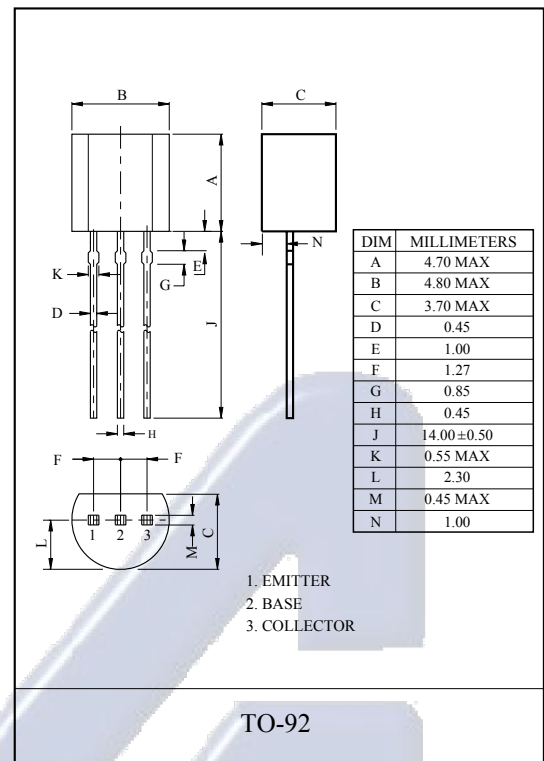
HIGH CURRENT APPLICATION.

### FEATURE

- Complementary to MPS8050.

### MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	-40	V
Collector-Emitter Voltage	$V_{CEO}$	-25	V
Emitter-Base Voltage	$V_{EBO}$	-6	V
Collector Current	$I_C$	-1.5	A
Collector Power Dissipation	$P_C$	625	mW
Junction Temperature	$T_j$	150	°C
Storage Temperature Range	$T_{stg}$	-55 ~ 150	°C



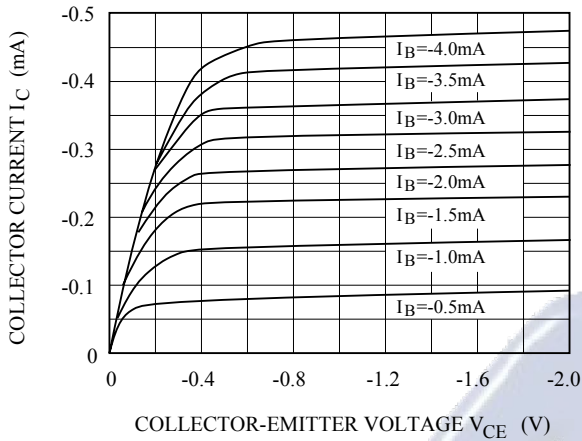
### ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB}=-35V, I_E=0$	-	-	-100	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=-6V, I_C=0$	-	-	-100	nA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-40	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-2mA, I_B=0$	-25	-	-	V
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-1V, I_C=-5mA$	45	170	-	
	$h_{FE(2)}$ (Note)	$V_{CE}=-1V, I_C=-100mA$	85	160	300	
	$h_{FE(3)}$	$V_{CE}=-1V, I_C=-800mA$	40	80	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-800mA, I_B=-80mA$	-	-0.28	-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-800mA, I_B=-80mA$	-	-0.98	-1.2	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE}=-1V, I_C=-10mA$	-	-0.66	-1.0	V
Transition Frequency	$f_T$	$V_{CE}=-10V, I_C=-50mA$	100	200	-	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=-10V, f=1MHz, I_E=0$	-	15	-	pF

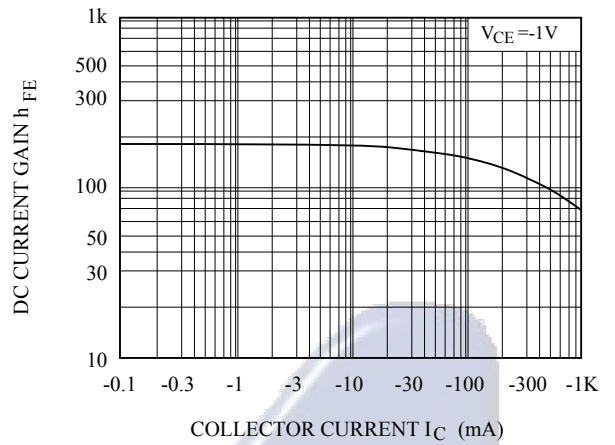
Note :  $h_{FE(2)}$  Classification B:85 ~ 160 , C: 120 ~ 200 , D: 160 ~ 300

# MPS8550

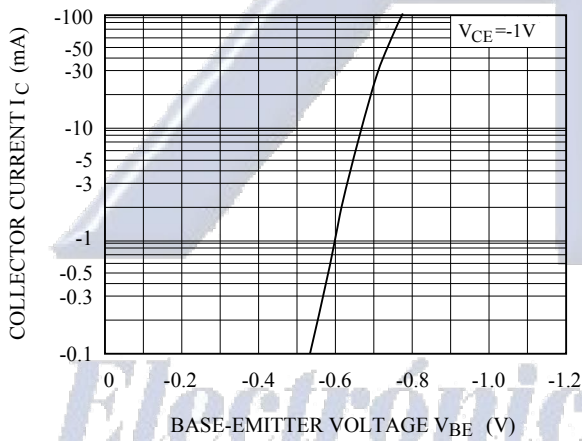
$I_C - V_{CE}$



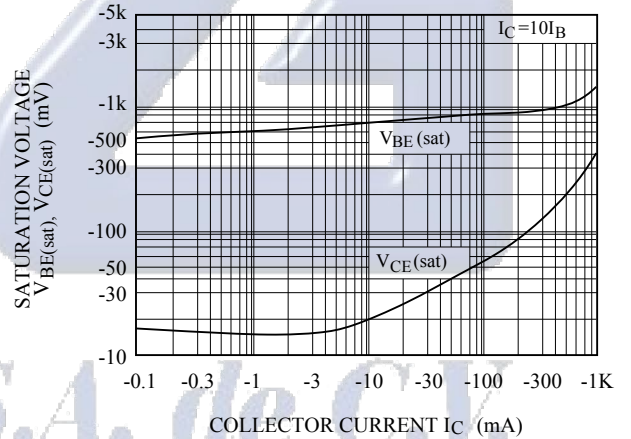
$h_{FE} - I_C$



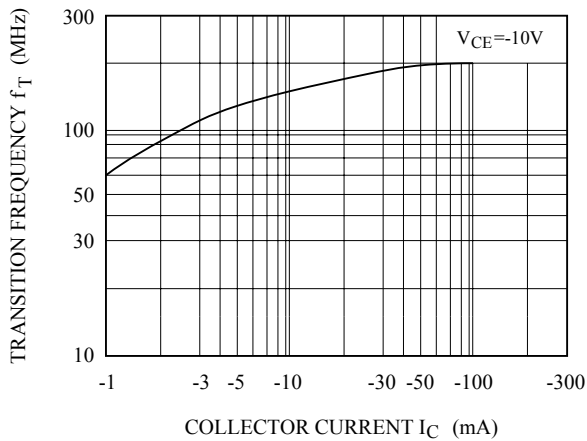
$I_C - V_{BE}$



$V_{BE(sat)}, V_{CE(sat)} - I_C$



$f_T - I_C$



$C_{ob} - V_{CB}$

